

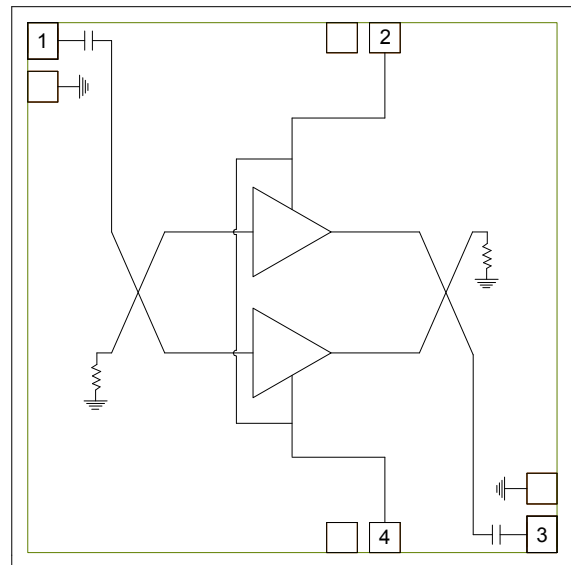
Features

- ▶ Low noise figure
- ▶ High gain broadband performance
- ▶ Excellent return losses
- ▶ Single positive supply voltage
- ▶ Small die size

Description

The CMD223 is a broadband MMIC low noise amplifier ideally suited for EW and communication systems where small size and low power consumption are needed. At 13.5 GHz the device delivers greater than 22 dB of gain with a corresponding output 1 dB compression point of +13.5 dBm and a noise figure of 1.5 dB. The CMD223 is a 50 ohm matched design eliminating the need for external DC blocks and RF port matching. The CMD223 offers full passivation for increased reliability and moisture protection.

Functional Block Diagram



Electrical Performance - $V_{dd} = 4\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$, $F = 13.5\text{ GHz}$

Parameter	Min	Typ	Max	Units
Frequency Range	9 - 18			GHz
Gain		22		dB
Noise Figure		1.5		dB
Input Return Loss		12		dB
Output Return Loss		13		dB
Output P1dB		13.5		dBm
Supply Current		93		mA



CMD223

9-18 GHz Balanced Low Noise Amplifier

Specifications

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, Vdd	5.5 V
RF Input Power	+23 dBm
Channel Temperature, Tch	150 °C
Power Dissipation, Pdiss	604 mW
Thermal Resistance	107 °C/W
Operating Temperature	-55 to 85 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the maximum ratings may cause permanent damage.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
Vdd	3.0	4.0	5.0	V
Idd		93		mA

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

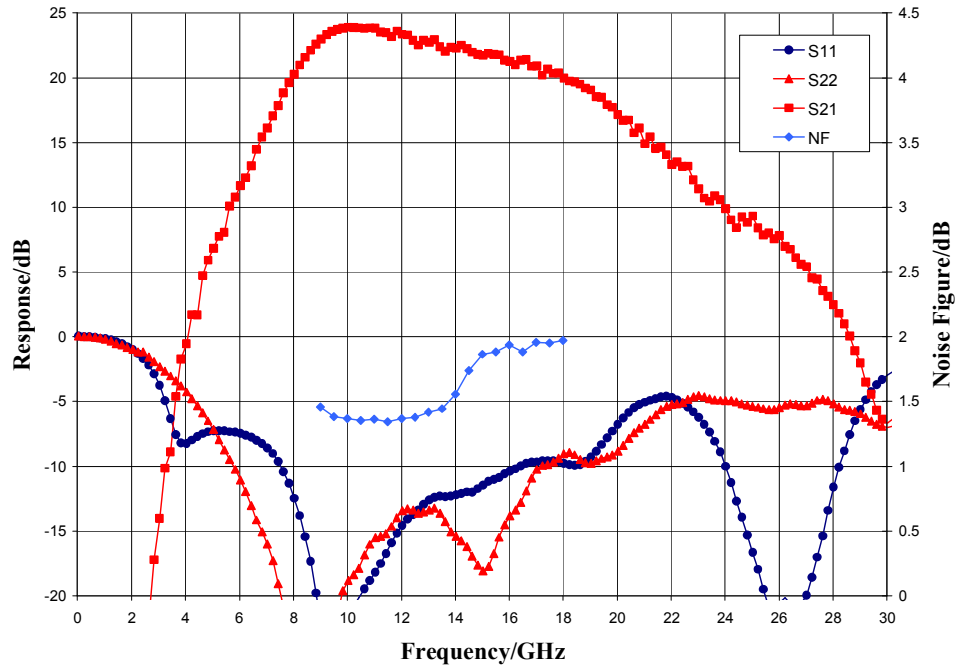
Electrical Specifications - V_{dd} = 4 V, T_A = 25 °C

Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range	9 - 14			14 - 18			GHz
Gain	19	23	26	17	21	25	dB
Noise Figure		1.4	1.8		1.9	2.3	dB
Input Return Loss		15			10		dB
Output Return Loss		15			14		dB
Output P1dB		10.5			15		dBm
Output IP3		21			22.5		dBm
Supply Current	65	93	121	65	93	121	mA
Gain Temperature Coefficient		0.017			0.017		dB/°C
Noise Figure Temperature Coefficient		0.009			0.009		dB/°C

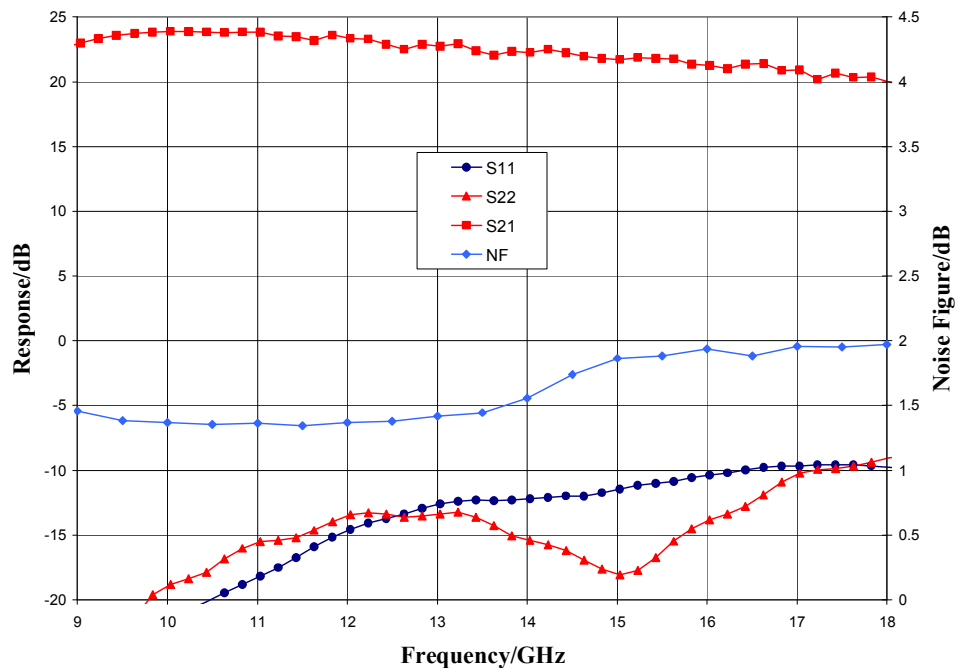
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Typical Performance

Broadband Performance, $V_{dd} = 4\text{ V}$, $I_{dd} = 93\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



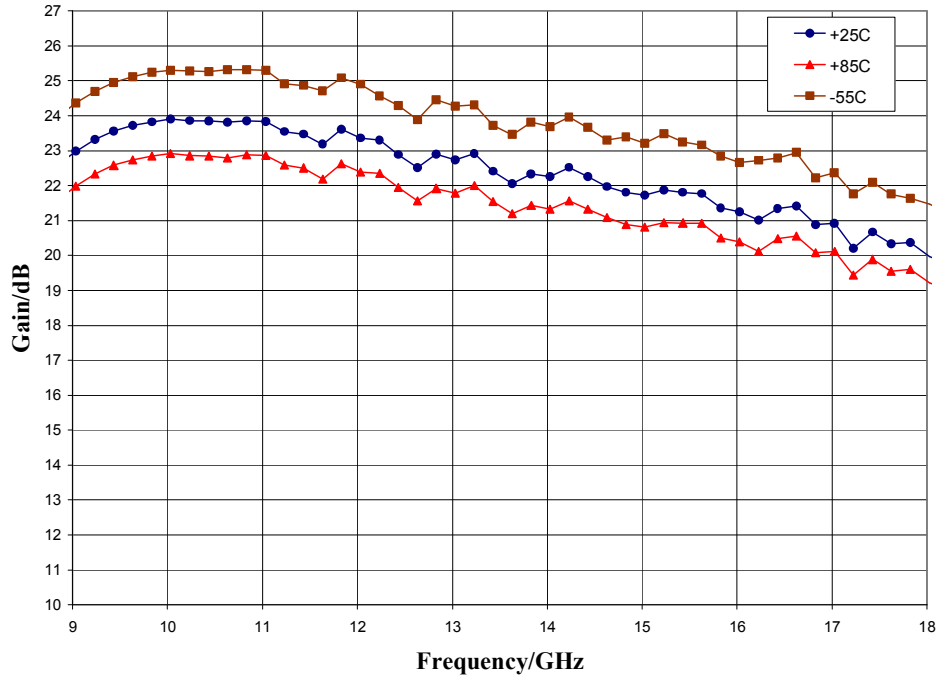
Narrow-band Performance, $V_{dd} = 4\text{ V}$, $I_{dd} = 93\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



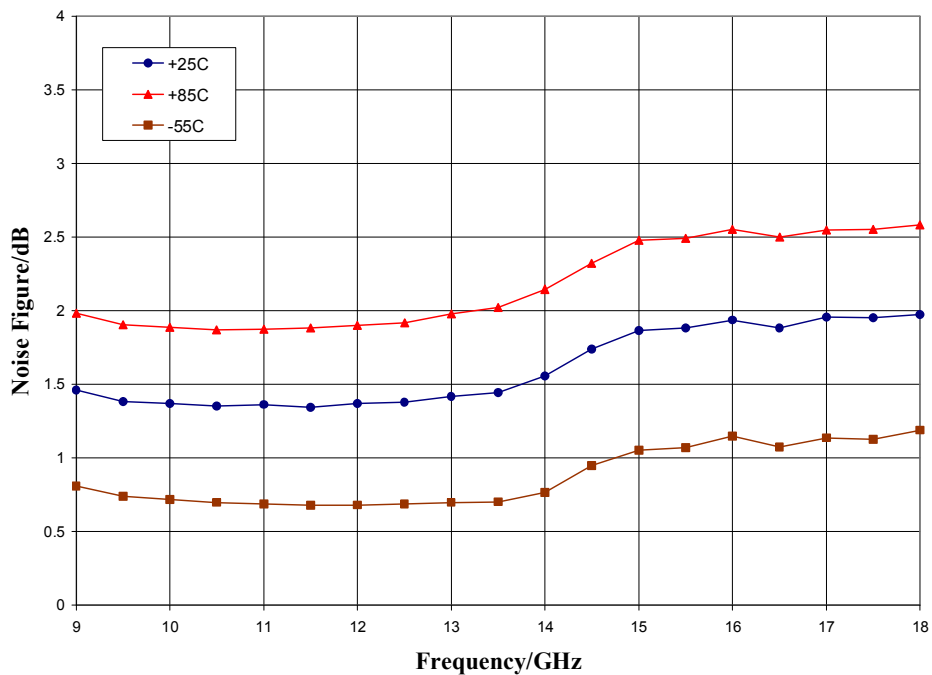
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Typical Performance

Gain vs. Temperature, $V_{dd} = 4\text{ V}$



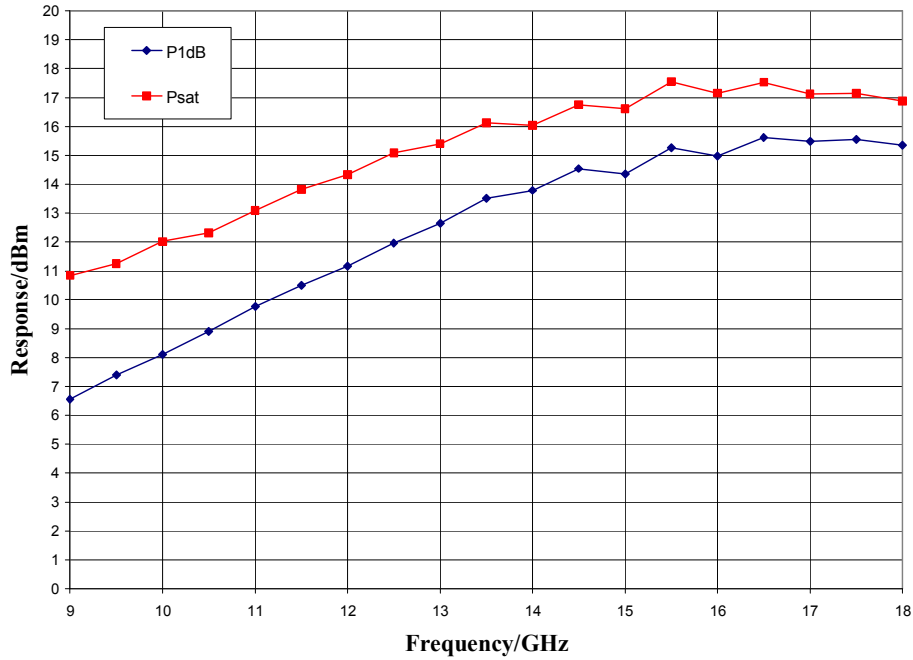
Noise Figure vs. Temperature, $V_{dd} = 4\text{ V}$



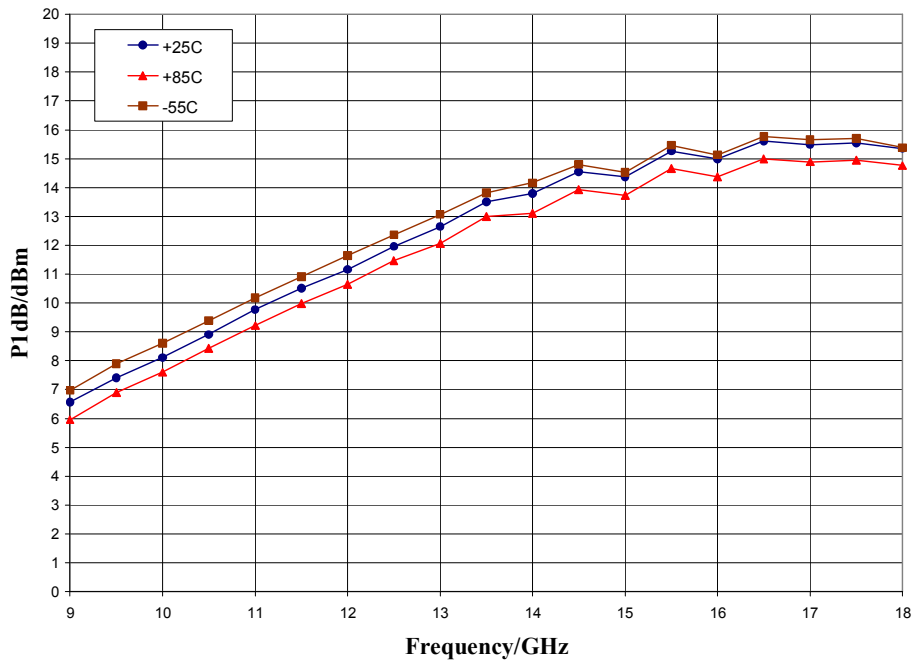
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Typical Performance

Output Power, $V_{dd} = 4\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$



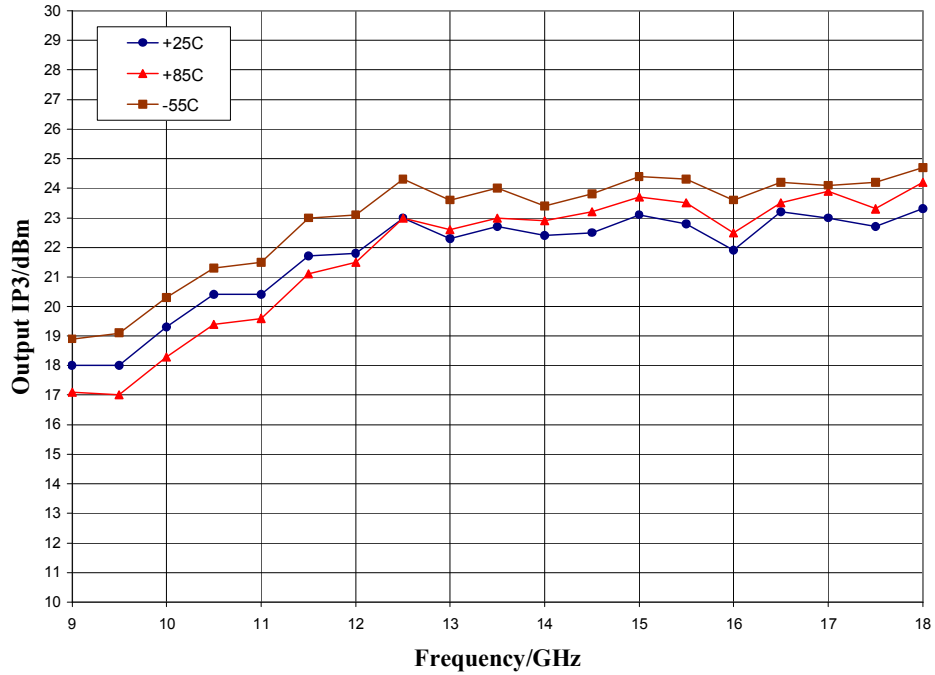
P1dB vs. Temperature, $V_{dd} = 4\text{ V}$



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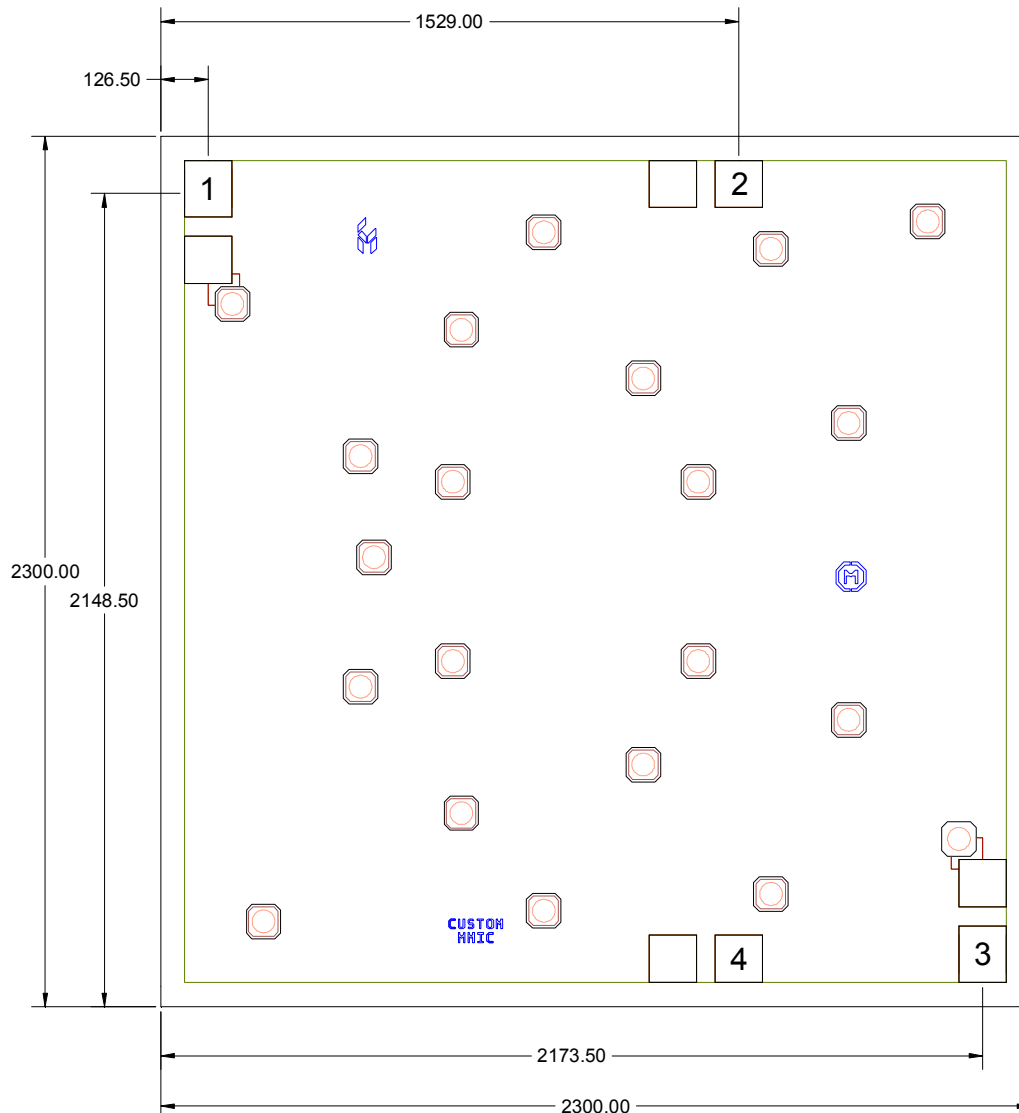
Typical Performance

Output IP3 vs. Temperature, $V_{dd} = 4\text{ V}$



Mechanical Information

Die Outline (all dimensions in microns)



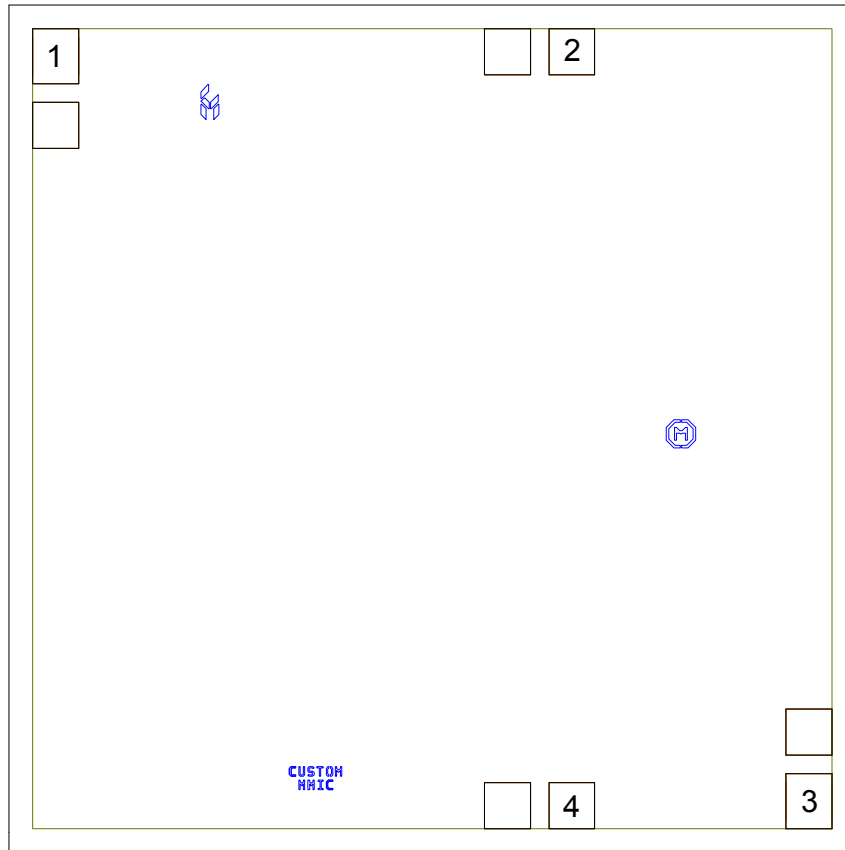
Notes:

1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 85 microns thick
5. DC bond pads are 100 microns square


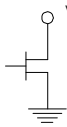


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Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1	RF in	DC blocked and 50 ohm matched	
2, 4	Vdd, Vdd-Optional	Power supply voltage Decoupling and bypass caps required. Only one of these pads need be connected to DC power supply.	
3	RF out	DC blocked and 50 ohm matched	
Backside	Ground	Connect to RF / DC ground	

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Applications Information

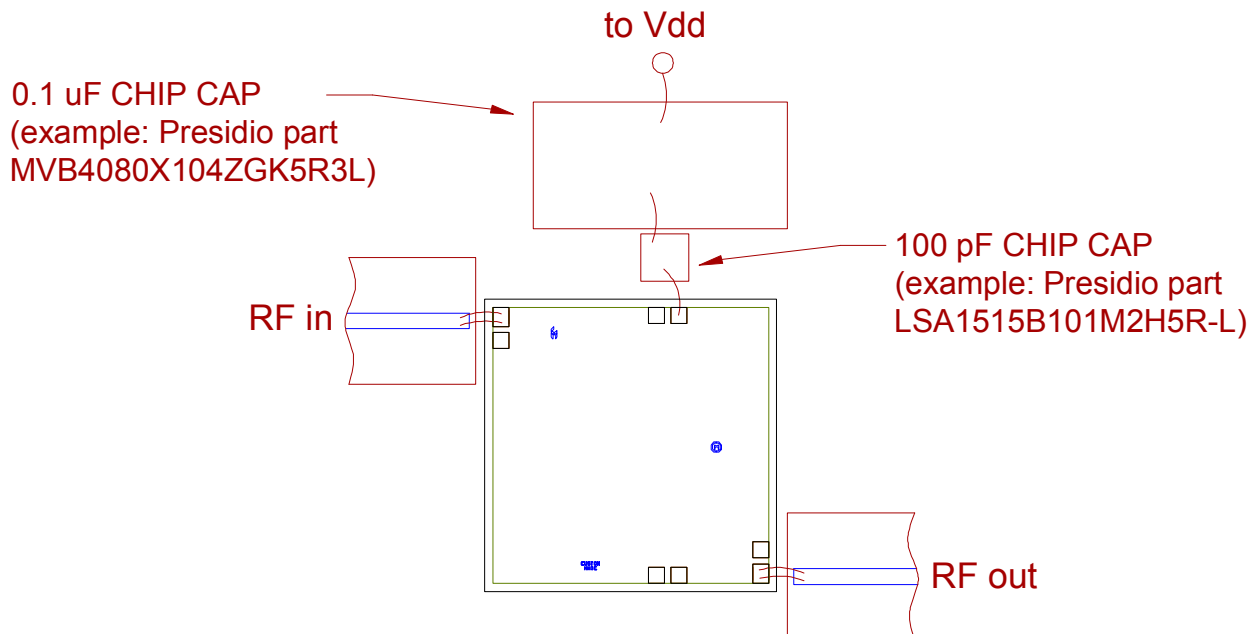
Assembly Guidelines

The backside of the CMD223 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 85 μm thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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CMD223

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Applications Information

Biasing and Operation

The CMD 223 is biased with a positive drain supply. Performance is optimized when the drain voltage is set to +4 V, though it may be set to a minimum of +2.0 V and a maximum of +5 V.

Turn ON procedure:

1. Apply drain voltage V_{dd} and set to +4 V

Turn OFF procedure:

1. Turn off drain voltage V_{dd}

RF power can be applied at any time.